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10/732,979	12/11/2003		Axel Brintzinger	2002 P 09238 US	8578
48154	7590	09/22/2006		EXAMINER	
SLATER &	-		NGUYEN, DILINH P		
17950 PRESTON ROAD SUITE 1000				ART UNIT	PAPER NUMBER
DALLAS,		2	2814		

DATE MAILED: 09/22/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
	10/732,979	BRINTZINGER, AXEL					
Office Action Summary	Examiner	Art Unit					
	DiLinh Nguyen	2814					
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
 Responsive to communication(s) filed on 23 Jule This action is FINAL. Since this application is in condition for allower closed in accordance with the practice under E 	action is non-final. nce except for formal matters, pro						
Disposition of Claims							
4) ☐ Claim(s) 1-5,8-10,28 and 31-34 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-5,8-10,28 and 31-34 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or election requirement.							
Application Papers							
 9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152. 							
Priority under 35 U.S.C. § 119		·					
 12) ⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) ⊠ All b) ☐ Some * c) ☐ None of: 1. ☒ Certified copies of the priority documents have been received. 2. ☐ Certified copies of the priority documents have been received in Application No 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal F 6) Other:	ate					

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-5, 8-10, 28 and 31-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nishiyama (U.S. Pat. 6107685) (previously applied) in view of Joshi et al. (U.S. Pat. 6731003) (previously applied).

Nishiyama discloses an electronic component comprising:

a wafer 20;

a plurality of bond pads 24 disposed on a surface of the wafer;

a plurality of functional 3-D structures (a plurality of bumps are arranged in the middle portion of the wafer 20) disposed on the surface of the wafer 20, each functional 3-D structure including a compliant base element and having an upper surface spaced from the surface of the wafer;

a plurality of selected 3-D structures (a plurality of bumps are arranged in the edge region of the wafer) disposed on the surface of the wafer to provide a mechanical reinforcement, wherein at least some of the selected 3-D structures have a greater mechanical load-bearing capacity than some of the functional 3-D structures (figs. 2A-2B).

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Nishiyama does not disclose a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto the upper surface of one of the functional 3D structure so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the functional 3-D structure.

However, Joshi et al. disclose an electronic component comprising a functional 3-D structure and a plurality of reroute traces 24 and 26 extending over the surface of the semiconductor die 18, each reroute trace being electrically connected to one of the bond pad 32 extending onto the upper surface of one of the functional 3-D structure so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the functional 3-D structure (fig. 4, column 3, lines 45-52). Therefore, it would have been obvious to one having ordinary in the art at the time the invention was made to modify the device structure of Nishiyama by having a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto a surface of one of the functional 3D structure because as taught by Joshi et al., such the plurality of reroute traces would provide higher resistance and increase likelihood for the semiconductor package (column 6, lines 4-8).

- Regarding claim 2, Joshi et al. disclose that wherein each reroute trace comprises a nickel layer 24 that is covered by a gold layer 26 (fig. 4, column 3, lines 62-63 and column 4, lines 1-2).
- Regarding claims 3 and 31, Nishiyama et al. disclose that the selected 3-D structures have a greater height than the functional 3-D structures (fig. 2B);

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therefore, the selected 3-D structures would have a lower degree of compressibility than the functional 3-D structures.

- Regarding claim 4, Nishiyama et al. disclose that the selected 3-D structures (a
 plurality of bumps are arranged in the edge region of the wafer) have a greater
 height than the functional 3-D structures (fig. 2B).
- Regarding claim 5, Nishiyama et al. disclose that each of the selected 3-D
 structures (a plurality of bumps are arranged in the edge region of the wafer)
 includes a compliant base element that has a significantly greater volume than
 the compliant base element of the functional 3-D structures (figs. 2A-2B).
- Regarding claims 8 and 32, Nishiyama et al. disclose that the selected 3-D structures (a plurality of bumps are arranged in the edge region of the wafer) are arranged in a regularly distributed manner in an edge region of the wafer 20 (fig. 2A).
- Regarding claims 9 and 33, Nishiyama et al. disclose that the selected 3-D structures are arranged in a regularly distributed manner over the wafer 20 (figs. 2A-2B).
- Regarding claim 10, Nishiyama et al. disclose that the selected 3-D structures are able to be electrically bonded (fig. 2B).
- Regarding claim 28, Nishiyama discloses an electronic component comprising:
 a wafer 20;
 - a plurality of bond pads 24 disposed on the wafer;

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a plurality of functional 3-D structures (a plurality of bumps are arranged in the middle portion of the wafer 20) disposed on the wafer 20, each functional 3-D structure including a compliant base element and having a first height; and

a plurality of other 3-D structures (a plurality of bumps are arranged in the edge region of the wafer (the lands 22a with bumps) or a plurality of reinforcing bumps 23 provided at four corners) disposed on the wafer to provide a mechanical reinforcement, each of the other 3-D structures having a second height that is greater than the first height (figs. 1A-1B, column 7, lines 35-55).

Nishiyama does not disclose a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto a surface of one of the functional 3D structure.

However, Joshi et al. disclose an electronic component comprising a functional 3-D structure and a plurality of reroute traces 24 and 26, each reroute trace being electrically connected to one of the bond pad 32 extending onto a surface of one of the functional 3-D structure (fig. 4, column 3, lines 45-52). Therefore, it would have been obvious to one having ordinary in the art at the time the invention was made to modify the device structure of Nishiyama by having a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto a surface of one of the functional 3D structure because as taught by Joshi et al., such the plurality of reroute traces would provide higher resistance and increase likelihood for the semiconductor package (column 6, lines 4-8).

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3. Claims 1, 3-5, 8-10 and 34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nishiyama (U.S. Pat. 6107685) (previously applied) in view of Matsuda et al. (U.S. Pat. 5666270) (newly cited).

Nishiyama discloses an electronic component comprising:

a wafer 20;

a plurality of bond pads 24 disposed on a surface of the wafer;

a plurality of functional 3-D structures (a plurality of bumps are arranged in the middle portion of the wafer 20) disposed on the surface of the wafer 20, each functional 3-D structure including a compliant base element and having an upper surface spaced from the surface of the wafer;

a plurality of selected 3-D structures (a plurality of bumps are arranged in the edge region of the wafer) disposed on the surface of the wafer to provide a mechanical reinforcement, wherein at least some of the selected 3-D structures have a greater mechanical load-bearing capacity than some of the functional 3-D structures (figs. 2A-2B).

Nishiyama does not disclose a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto the upper surface of one of the functional 3D structure so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the functional 3-D structure.

However, Matsuda et al. disclose an electronic component comprising:

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a plurality of reroute traces 36 extending over a surface of the semiconductor chip 31, each reroute trace being electrically connected to one of a bond pads 32 and extending onto an upper surface of one of the functional 3-D structure 35 so that the reroute tract provides an electrical connection between the bond pad 32 and the upper surface of the functional 3-D structure (fig. 5, column 3, lines 54-60). Therefore, it would have been obvious to one having ordinary in the art at the time the invention was made to modify the device structure of Nishiyama by having a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto the upper surface of one of the functional 3D structure because as taught by Matsuda et al., such reroute trace would protect the core part of the bump (fig. 5).

- Regarding claim 3, Nishiyama et al. disclose that the selected 3-D structures
 have a greater height than the functional 3-D structures (fig. 2B); therefore, the
 selected 3-D structures would have a lower degree of compressibility than the
 functional 3-D structures.
- Regarding claim 4, Nishiyama et al. disclose that the selected 3-D structures (a
 plurality of bumps are arranged in the edge region of the wafer) have a greater
 height than the functional 3-D structures (fig. 2B).
- Regarding claim 5, Nishiyama et al. disclose that each of the selected 3-D structures (a plurality of bumps are arranged in the edge region of the wafer) includes a compliant base element that has a significantly greater volume than the compliant base element of the functional 3-D structures (figs. 2A-2B).

Regarding claim 8, Nishiyama et al. disclose that the selected 3-D structures (a
plurality of bumps are arranged in the edge region of the wafer) are arranged in a
regularly distributed manner in an edge region of the wafer 20 (fig. 2A).

- Regarding claim 9, Nishiyama et al. disclose that the selected 3-D structures are arranged in a regularly distributed manner over the wafer 20 (figs. 2A-2B).
- Regarding claim 10, Nishiyama et al. disclose that the selected 3-D structures are able to be electrically bonded (fig. 2B).
- Regarding claim 34, Masuda et al. disclose that the compliant base element 35 is formed from silicone (fig. 5, column 3, lines 56-57).
- 4. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nishiyama (U.S. Pat. 6107685) (previously applied) in view of Matsuda et al. (U.S. Pat. 5666270) (newly cited) as applied to claim 1 above, and further in view of Joshi et al. (U.S. Pat. 6731003) (previously applied).

Nishiyama in view of Matsuda et al. substantially disclose all the limitations as claimed above except for each reroute trace comprises a copper/nickel layer that is covered by a gold layer.

However, Joshi et al. disclose an electronic component comprising a functional 3-D structure and a plurality of reroute traces 24 and 26 extending over the surface of the semiconductor die 18, wherein each reroute trace comprises a nickel layer 24 that is covered by a gold layer 26 (fig. 4, column 3, lines 62-63 and column 4, lines 1-2). Therefore, it would have been obvious to one having ordinary in the art at the time the invention was made to modify the device structure of Nishiyama in view of Matsuda et

al. by having the reroute trace comprises a copper/nickel layer that is covered by a gold layer because as taught by Joshi et al., such the nickel layer that is covered by a gold layer for the reroute trace would provide higher resistance for the semiconductor package (column 6, lines 4-8).

Response to Arguments

Applicant's arguments filed 6/23/06 have been fully considered but they are not persuasive.

 The applicant argues that neither Nishiyama nor Joshi teach or suggest a compliant base element.

The arguments have been fully considered but they are not persuasive because Nishiyama clearly discloses a plurality of functional 3-D structures (a plurality of bumps are arranged in the middle portion of the wafer 20) disposed on the surface of the wafer 20 (figs. 2A-2B), each functional 3-D structure including a compliant base element 31 (fig. 3D). Joshi et al. also disclose a plurality of functional 3-D structures disposed on the surface of the semiconductor chip 18, each functional 3-D structure including a compliant base element 22 (figs. 1 and 4).

• The applicant argues that Joshi et al. do not disclose a plurality of reroute traces, each reroute trace being electrically connected to one of the bond pad and extending onto the upper surface of one of the functional 3D structure so that the reroute trace provides an electrical connection between the bond pad and the upper surface of the functional 3-D structure.

The arguments have been fully considered but they are not persuasive because Joshi et al. disclose an electronic component comprising a functional 3-D structure and a plurality of reroute traces 24 and 26 extending over the surface of the semiconductor die 18, each reroute trace being electrically connected to one of the bond pad 32 extending onto the upper surface of one of the functional 3-D structure so that the reroute trace (the copper element 22, the nickel layer 24 and the gold layer 26 are electrically connected to the bond pad 32) provides an electrical connection between the bond pad and the upper surface of the functional 3-D structure (fig. 4, column 3, lines 45-52).

• The applicant argues that Nishiyama fails to disclose a plurality of other 3-D structures disposed on the wafer, each of the other 3-D structures having a second height that is greater than the first height.

The arguments have been fully considered but they are not persuasive because Nishiyama discloses that a plurality of other 3-D structures (a plurality of bumps are arranged in the edge region of the wafer (the lands 22a with bumps) or a plurality of reinforcing bumps 23 provided at four corners) disposed on the wafer to provide a mechanical reinforcement, each of the other 3-D structures having a second height that is greater than the first height (a plurality of bumps are arranged in the middle portion of the wafer 20 have first height) (figs. 1A-1B, column 7, lines 35-55).

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to DiLinh Nguyen whose telephone number is (571) 272-1712. The examiner can normally be reached on 8:00AM - 6:00PM (M-F).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

DLN

HOAI FHAM
PRIMARY EXAMINER